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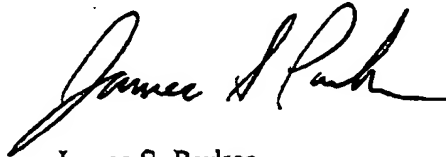
Docket No. UF-222XC2D2
Serial No. 09/735,217Remarks

Claims 1-11 were pending in the subject application. By way of this amendment, claims 2-11 have been amended to correct typographical dependency errors. Therefore, claims 2-11 are pending and currently before the Examiner for consideration. Applicants confirm that no new matter has been entered by this amendment.

The Commissioner is hereby authorized to charge to Deposit Account 19-0065 any fees under 37.CFR 1.16 or 1.17 as required by this paper.

Applicants invite the Examiner to call the undersigned if clarification is needed on any of this amendment, or if the Examiner believes a telephone interview would expedite the prosecution of the subject application to completion.

Respectfully submitted,



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Docket No. UF-222XC2D2
Serial No. 09/735,217Marked-Up Claim(s)

1 2. The device according to claim [40] 1, wherein said device can transition from
2 MOVPE to HVPE *in situ*.

1 3. The device according to claim [41] 2, wherein the substrate does not have to be
2 removed from the device between MOVPE and HVPE.

1 4. The device according to claim [42] 3, wherein the substrate can be maintained at
2 elevated temperatures during transition from MOVPE to HVPE.

1 5. The device according to claim [41] 2, wherein said device can also transition from
2 HVPE to MOVPE *in situ*.

1 6. The device according to claim [44] 5, wherein said device can also transition from
2 HVPE to MOVPE *in situ*.

1 7. The device according to claim [45] 6, wherein the substrate can be maintained at
2 elevated temperatures during transition from HVPE to MOVPE.

1 8. The device according to claim [40] 1, wherein said device can be used to grow a
2 III-V nitride compound semiconductor onto the surface of the substrate.

1 9. The device according to claim [47] 8, wherein said device can be used to grow GaN
2 onto the surface of the substrate.

1 10. The device according to claim [48] 9, wherein said means for performing HVPE
2 comprises a hot wall reactor having a source zone, and
3 a downstream mixing zone,

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4 wherein TMG can be reached with Hcl in the source zone to form a chlorinated ⁶gallium
LAK 5 species, and wherein the chlorinated ⁶gallium species can combine with NH₃ in the downstream
6 mixing zone and directed toward the substrate for deposition of GaN onto the substrate.

1 11. The device according to claim [48] 9, wherein said means for performing MOVPE
LAK 2 comprises a low pressure ~~horizontal~~ cold-wall MOCVD reactor.

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